NSN 5961-01-581-2519

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No Fiig: A110a0



View Online at https://aerobasegroup.com/nsn/5961-01-581-2519 **Inclosure Material:** Glass **End Application:** Ca70608-00 (19156), receiver-transmitter **Mounting Facility Quantity:** 2 **Mounting Method:** Unthreaded hole **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 60.0 collector to emitter voltage, dc and 4.0 emitter to base voltage, dc **Current Rating Per Characteristic:** 1.00 amperes collector current, dc **Power Rating Per Characteristic:** 50.0 watts forward power dissipation, dc and 7.0 watts power output **Product Name:** Dwg: rf transistor; cage: 7 watts, 50 volts, pulsed avionics 960 - 1215 mhz, common base bipolar transistor **Precious Material And Location:** Thin film metallization gold Shelf Life: N/a **Unit Of Measure: Demilitarization:**